1.8V Drive Nch MOSFET RUF015N02

●Structure

Silicon N-channel MOSFET

● Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TUMT3).
- 3) Low voltage drive (1.8V drive).

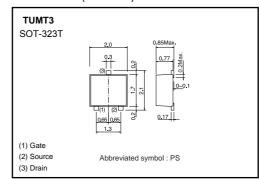
Applications

Switching

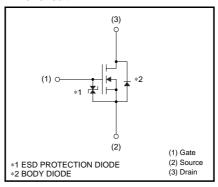
Packaging specifications

	Package	Taping	
Type	Code	TL	
	Basic ordering unit (pieces)	3000	
RUF015N02	0		

●Dimensions (Unit:mm)



●Inner circuit



● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		VDSS	20	V	
Gate-source voltage		V _{GSS}	10	V	
Drain current	Continuous	I _D	±1.5	А	
Drain current	Pulsed	I _{DP} *1	±3.0	A	
Source current	Continuous	Is	0.6	A	
(Body diode)	Pulsed	I _{SP} *1	2.4	Α	
Total power dissipation		P _D *2	0.8	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

^{*1} Pw≤10μs, Duty cycle≤1% *2 Mounted on a ceramic board

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	156	°C/W

^{*} Mounted on a ceramic board

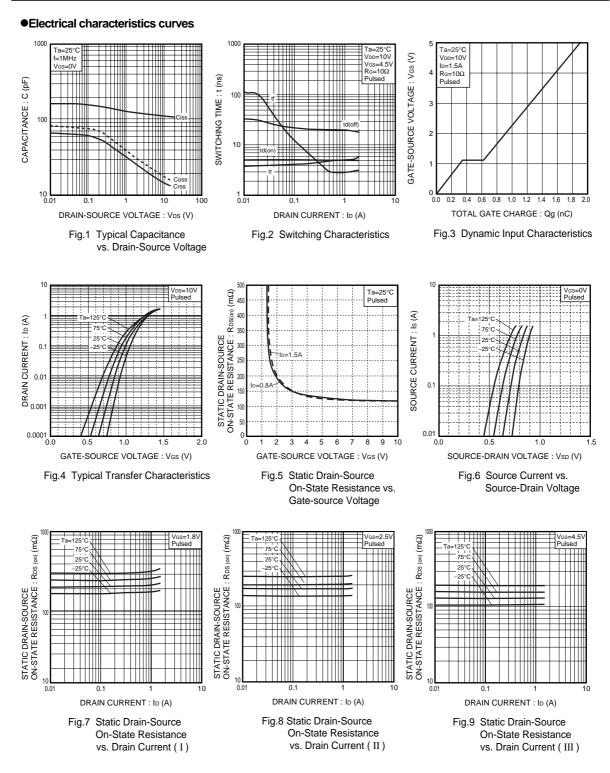
●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	_	-	10	μΑ	V _{GS} =10V, V _{DS} =0V
Drain-source breakdown voltage	V _(BR) DSS	20	-	_	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	V _{DS} = 20V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.3	_	1.0	V	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance		_	130	180	mΩ	ID= 1.5A, VGS= 4.5V
	R _{DS (on)} *	-	170	240	mΩ	I _D = 1.5A, V _{GS} = 2.5V
		-	220	310	mΩ	I _D = 0.8A, V _{GS} = 1.8V
Forward transfer admittance	Y _{fs} *	1.6	-	-	S	V _{DS} = 10V, I _D = 1.5A
Input capacitance	Ciss	_	110	_	pF	V _{DS} = 10V
Output capacitance	Coss	-	18	_	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	-	15	_	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	-	5	-	ns	ID= 1.0A
Rise time	tr *	_	5	_	ns	VDD≒ 10V
Turn-off delay time	t _{d (off)} *	_	20	_	ns	V _{GS} = 4.5V R _L =10Ω
Fall time	t _f *	-	3	_	ns	R _G =10Ω
Total gate charge	Qg *	-	1.8	2.5	nC	V _{DD} ≒10V
Gate-source charge	Qgs *	_	0.3	_	nC	Vgs= 4.5V
Gate-drain charge	Q _{gd} *	-	0.3	_	nC	I _D = 1.5A

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	_	_	1.2	V	I _S = 0.6A, V _{GS} =0V



●Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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